

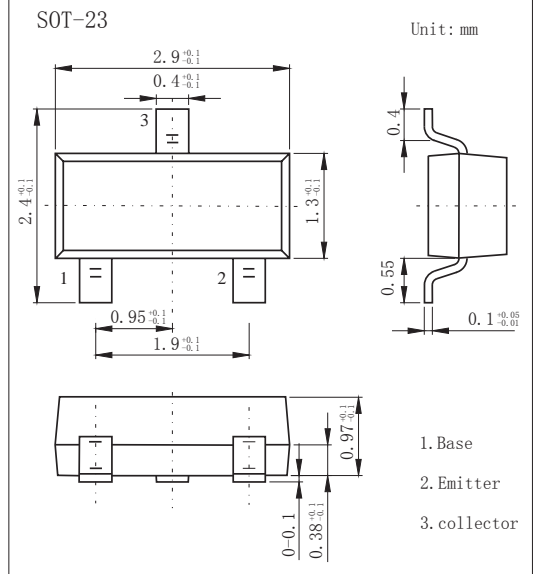
## SOT-23 Plastic-Encapsulate Transistors

### Features

- 625mW power dissipation.
- IC CONT 2.5A.
- IC up to 10A peak pulse current.
- Excellent hfe characteristics up to 10A (pulsed).
- Extremely low saturation voltage e.g. 10mV typ..
- Exhibits extremely low equivalent on-resistance; RCE(sat) .
- PNP Transistors

### MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	-20	V
Collector - Emitter Voltage	V <sub>CEO</sub>	-20	
Emitter - Base Voltage	V <sub>EBO</sub>	-5	
Collector Current - Continuous	I <sub>C</sub>	-1.5	A
Peak Collector Current	I <sub>CM</sub>	-6	
Base Current	I <sub>B</sub>	-500	mA
Collector Power Dissipation	P <sub>C</sub>	625	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature range	T <sub>stg</sub>	-55 to 150	

### PACKAGE INFORMATION

Device	Package	Shipping
FMMT718	SOT-23	3000/Tape&Reel

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100uA	-20	-65		V
Collector-emitter breakdown voltage *	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-10mA	-20	-55		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100uA	-5	-8.8		V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> =-15V			-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V			-100	nA
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>C</sub> =-0.1A, I <sub>B</sub> =-10mA I <sub>C</sub> =-1A, I <sub>B</sub> =-10mA I <sub>C</sub> =-1.5A, I <sub>B</sub> =-50mA		-16 -130 -145	-40 -200 -220	mV
Base-emitter saturation voltage *	V <sub>BE(sat)</sub>	I <sub>C</sub> =-1.5A, I <sub>B</sub> =-50mA		-0.87	-1	V
Base-emitter voltage *	V <sub>BE(ON)</sub>	I <sub>C</sub> =-2A, V <sub>CE</sub> =-2V		-0.81	-1	V
DC current gain *	h <sub>FE</sub>	I <sub>C</sub> =-10mA, V <sub>CE</sub> =-2V I <sub>C</sub> =-0.1A, V <sub>CE</sub> =-2V I <sub>C</sub> =-2A, V <sub>CE</sub> =-2V I <sub>C</sub> =-4A, V <sub>CE</sub> =-2V I <sub>C</sub> =-6A, V <sub>CE</sub> =-2V	300 300 150 35 15	475 450 230 70 30		
Current-gain-bandwidth product	f <sub>T</sub>	I <sub>C</sub> =-50mA, V <sub>CE</sub> =-10V, f=100MHz	150	180		MHz
Output capacitance	C <sub>obo</sub>	V <sub>CB</sub> =-10V, f=1MHz		21	30	pF
Turn-on time	t <sub>(on)</sub>	V <sub>CC</sub> =-10V, I <sub>C</sub> =-1A		40		ns
Turn-off time	t <sub>(off)</sub>	I <sub>B1</sub> =-I <sub>B2</sub> =-20mA		670		ns

\* Pulse test: t<sub>p</sub> ≤ 300 is; d ≤ 0.02.

### Marking

Marking	718
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